

Silicon PNP Power Transistors

2N6491

DESCRIPTION

- With TO-220 package
- Complement to type 2N6488

APPLICATIONS

- It is intended for use in power linear and low frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

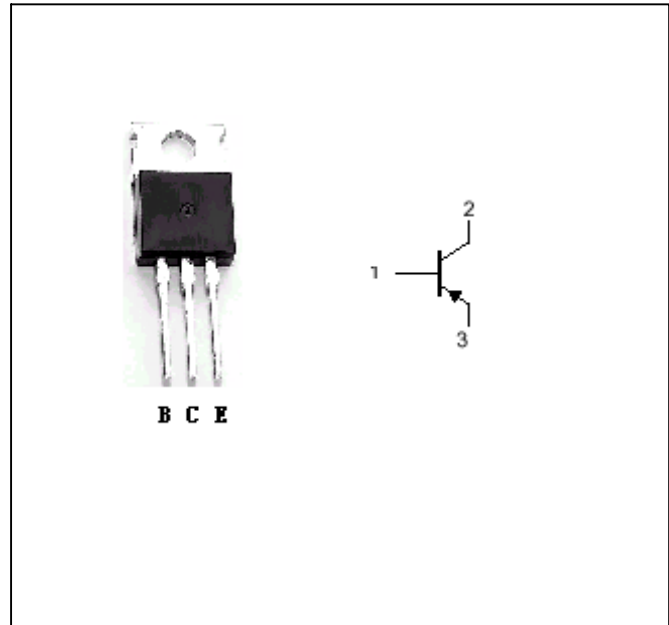


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	90	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _T	Total power dissipation	T _C =25	75	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.67	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	80			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5A I _B =0.5A			1.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =15A I _B =5A			3.5	V
V _{BE-1}	Base-emitter on voltage	I _C =5A ; V _{CE} =4V			1.3	V
V _{BE-2}	Base-emitter on voltage	I _C =15A ; V _{CE} =4V			3.5	V
I _{CEO}	Collector cut-off current	V _{CE} =40V; I _B =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA
h _{FE-1}	DC current gain	I _C =5A ; V _{CE} =4V	20		150	
h _{FE-2}	DC current gain	I _C =15A ; V _{CE} =4V	5			

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PACKAGE OUTLINE

